NSN 5962-01-368-3810

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-368-3810

Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Am-7315/spy-1 e/i fscm 02769

Features Provided:

Programmed

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

20 input

Case Outline Source And Designator:

D-9 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital fused pal

Voltage Rating And Type Per Characteristic:

4.5 volts positive power supply span and 5.5 volts positive power supply span

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Special Features:

Programmed per "bf6710168-2"

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). And 67268-84129 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Purchase Description Identification:

5371-16-710-1682

Chalf I ifar

NSN 5962-01-368-3810

Memory Microcircuit - Page 2 of 2

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

